

# AM6968N-T1-PF-VB Datasheet Dual N-Channel 25-V (D-S) MOSFET

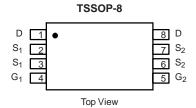
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
25	0.022 at V <sub>GS</sub> = 4.5 V	6.6		
	0.032 at V <sub>GS</sub> = 2.5 V	5.5		

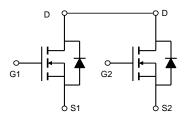
#### **FEATURES**

- Halogen-free Option Available
- TrenchFET® Power MOSFETs









<b>ABSOLUTE MAXIMUM RATINGS</b>	$T_A = 25$ °C, unles	s otherwise n	oted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	25		V	
Gate-Source Voltage		V <sub>GS</sub>	± 12		V	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	6.6	5.2	^	
	T <sub>A</sub> = 70 °C		5.5	3.5		
Pulsed Drain Current		I <sub>DM</sub>	30		Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.5	1.0		
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.5	1.0	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		0.96	0.64		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Manifesture Investigate As Aughtentia	t ≤ 10 s	R <sub>thJA</sub>	72	83	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	<b>'</b> `thJA	100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	55	70	

#### Notes:

a. Surface Mounted on FR4 board,  $t \le 10 \text{ s.}$ 

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<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply.



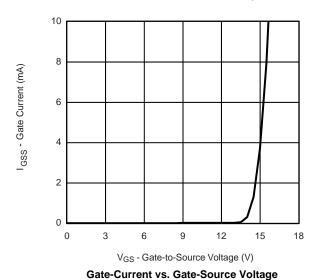
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	0.5		1.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$			1		
	IDSS	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			25	μA	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
Drain-Source On-State Resistance <sup>b</sup>	В	$V_{GS} = 4.5 \text{ V}, I_D = 6.5 \text{ A}$		0.022			
	R <sub>DS(on)</sub> –	$V_{GS} = 2.5 \text{ V}, I_D = 5.5 \text{ A}$		0.032		Ω	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6.5 A		30		S	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	I <sub>S</sub> = 1.5 A, V <sub>GS</sub> = 0 V		0.71	1.2	V	
Dynamic <sup>a</sup>							
Total Gate Charge	$Q_g$			12	18		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.5 \text{ A}$		2.2		nC	
Gate-Drain Charge	$Q_{gd}$			3.6			
Turn-On Delay Time	t <sub>d(on)</sub>			245	365		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$		330	495		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 4.5 V, $R_G$ = 6 $\Omega$		860	1300	ns	
Fall Time	t <sub>f</sub>			510	765		

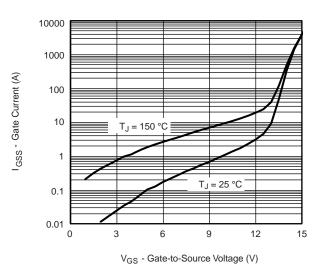
#### Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



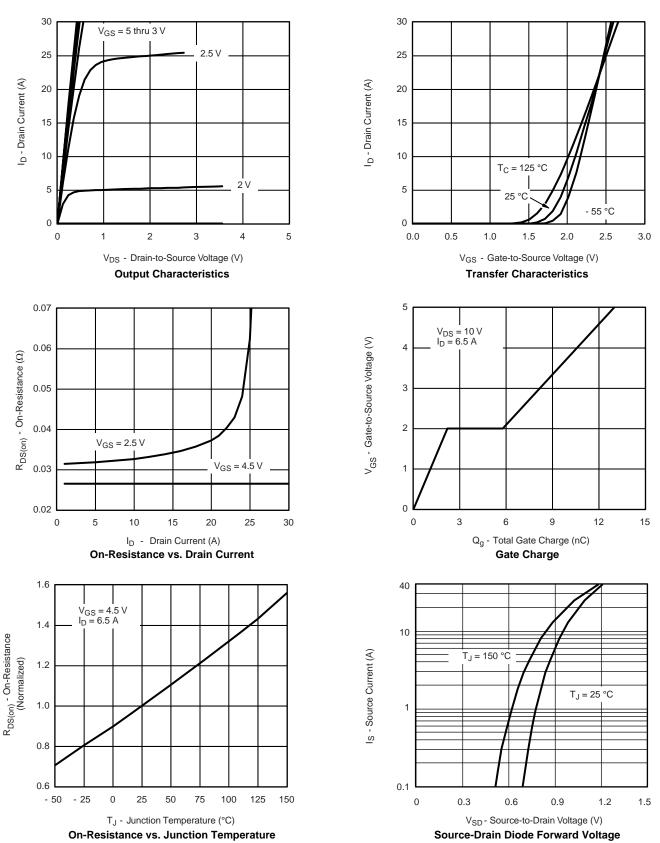


VGS - Gate-to-Source voltage (V)

Gate Current vs. Gate-Source Voltage

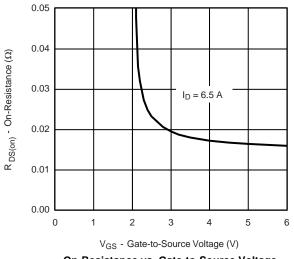


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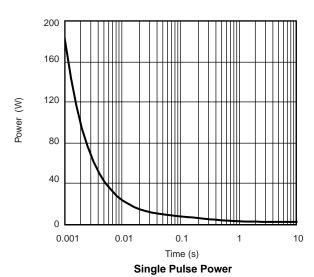




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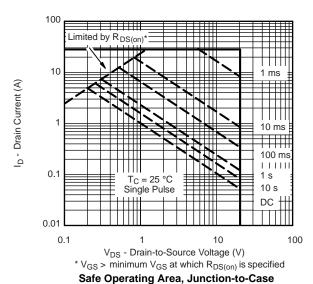


On-Resistance vs. Gate-to-Source Voltage

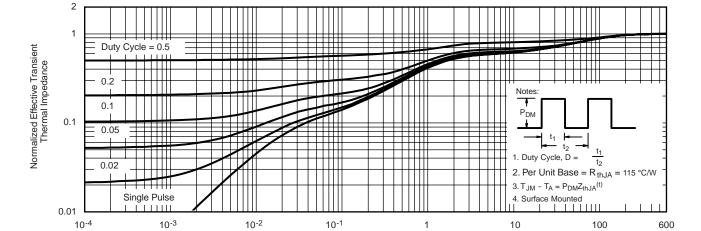


0.4 I<sub>D</sub> = 250 μA 0.2 V<sub>GS(th)</sub> Variance (V) 0.0 - 0.2 - 0.4 - 0.6 0 - 50 - 25 25 50 75 100 125 150 T<sub>J</sub> - Temperature (°C)

Threshold Voltage



10

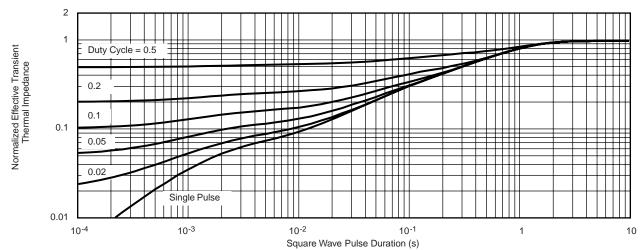


Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Ambient

100



#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

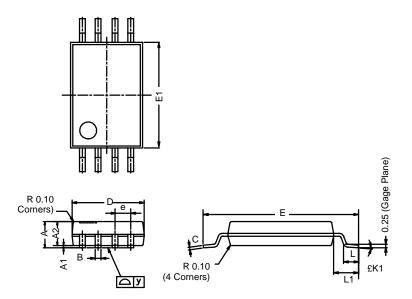


Normalized Thermal Transient Impedance, Junction-to-Foot



TSSOP: 8-LEAD

**JEDEC Part Number: MO-153** 

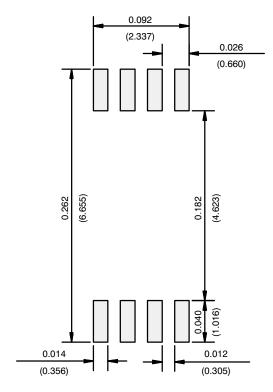


	MILLIMETERS				
Dim	Min	Nom	Max		
Α	-	-	1.20		
A <sub>1</sub>	0.05	0.10	0.15		
A <sub>2</sub>	0.80	1.00	1.05		
В	0.19	0.28	0.30		
С	-	0.127	-		
D	2.90	3.00	3.10		
Е	6.20	6.40	6.60		
E <sub>1</sub>	4.30	4.40	4.50		
е	_	0.65	-		
L	0.45	0.60	0.75		
L <sub>1</sub>	0.90	1.00	1.10		
Y	-	-	0.10		
£K1	0°	3°	6°		
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844					



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#### **RECOMMENDED MINIMUM PADS FOR TSSOP-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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